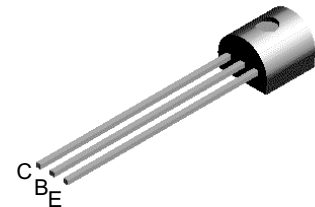


S9015-B
S9015-C
S9015-D

Features

- TO-92 Plastic-Encapsulate Transistors
- Capable of 0.45Watts($T_{amb}=25^{\circ}C$) of Power Dissipation.
- Collector-current -0.1A
- Collector-base Voltage -50V
- Operating and storage junction temperature range: $-55^{\circ}C$ to $+150^{\circ}C$
- Marking: S9015
- Lead Free Finish/RoHS Compliant ("P" Suffix designates RoHS Compliant. See ordering information)
- Epoxy meets UL 94 V-0 flammability rating
- Moisture Sensitivity Level 1



Electrical Characteristics @ 25°C Unless Otherwise Specified

Symbol	Parameter	Min	Max	Units
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OFF CHARACTERISTICS

$V_{(BR)CBO}$	Collector-Base Breakdown Voltage ($I_C = -100\mu A_{dc}, I_E = 0$)	-50	---	Vdc
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage ($I_C = -1.0mA_{dc}, I_B = 0$)	-45	---	Vdc
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ($I_E = -100\mu A_{dc}, I_C = 0$)	-5.0	---	Vdc
I_{CBO}	Collector Cutoff Current ($V_{CB} = -50V_{dc}, I_E = 0$)	---	-0.05	μA_{dc}
I_{EBO}	Emitter Cutoff Current ($V_{EB} = -5.0V_{dc}, I_C = 0$)	---	-0.05	μA_{dc}

ON CHARACTERISTICS

h_{FE}	DC Current Gain ($I_C = -1.0mA_{dc}, V_{CE} = -5.0V_{dc}$)	60	1000	---
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage ($I_C = -100mA_{dc}, I_B = -10mA_{dc}$)	---	-0.3	Vdc
$V_{BE(sat)}$	Base-Emitter Saturation Voltage ($I_C = -100mA_{dc}, I_B = -10mA_{dc}$)	---	-1.0	Vdc

SMALL-SIGNAL CHARACTERISTICS

f_T	Transistor Frequency ($I_C = -10mA_{dc}, V_{CE} = -5.0V_{dc}, f = 30MHz$)	150	---	MHz
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CLASSIFICATION OF h_{FE}

Rank	B	C	D
Range	100-300	200-600	400-1000

